1	L Number	Hits	Search Text	DB	Time stamp
Characteristic\$\$) same capacit\$\$ US-RGUB; EPO, JPO; DERMENT; IEM TDB USPAT; IEM TDB				1	
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3	2	1	("6636073").PN.	USPAT;	2004/03/18 10:35
1				US-PGPUB	
1	3	3	(("5107137") or ("5175445") or	USPAT;	2004/03/18 10:36
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Section	4	1	6636073.pn. and MIS		2004/03/18 10:37
6					
7	5	_			
3			1	F	
- 46 (("metal/insulator/semiconductor") or ("metal-insulator-semiconductor") or (capacitéa-voltage) or (capacitéa-vo		_		l .	I .
("metal-insulator-semiconductor") or characteristic\$5) same capacit\$5	8	•		1	
C'MIS") same ((("C-V") or (CV)) near3 characteristic\$5 same capacit\$5 CRMENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO	-	46			2004/03/18 10:26
Characteristic\$\$) same capacit\$\$ DERWENT; IBM TDB Comparison or ("metal-insulator/semiconductor") or ("metal-insulator-semiconductor") or (capacits4-voltage)					
The Top					
-			Characteristic(3) Same Capacit(3)	1	
("metal-insulator-semiconductor")or ("MIS") and ("LCR" adj meter) US-PGPUB; EPO, JPO; DERWENT; IBM TDB USPAT; US-FGPUB USPAT; US-FGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; USPAT	_	37	(("metal/insulator/semiconductor") or		2002/12/09 11:46
("MIS") and ("LCR" adj meter)]	, ,	1	
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1			<u>.</u>	1	
1	_	1	"4083254".PN.		2002/12/09 11:50
- 1					
- 1 "4681451".PN. 72 (("metal/insulator/semiconductor") or ("metal-insulator-semiconductor") or ("sp-pgub; "metal-insulator-semiconductor") o	-	1	"4322979".PN.		2002/12/09 11:50
- 72 (("metal/insulator/semiconductor") or ("metal-insulator-semiconductor") or ("metal-insulator-semiconductor") or ("metal-insulator-semiconductor") or ("ms")) same ((("C-V") or (CV) or (capacit\$4 avoltage) or (capacit\$4-voltage) or (capacit\$4/voltage)) near3 characteristic\$5) same capacit\$5 - 3 5701088.bi,uref. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; EPO; JPO; DERWENT; IBM_TDB USPAT; EPO; JPO; DERWEN				US-PGPUB	
- 72 (("metal/insulator/semiconductor") or ("metal-insulator-semiconductor") or ("metal-insulator-semiconductor") or ("metal-insulator-semiconductor") or ("SPAT; US-PGPUB; EPO; JPO; Capacit\$4 adj voltage) or (capacit\$4-voltage) or (capacit\$4-voltage) or (capacit\$4-voltage) or (capacit\$4-voltage) or (capacit\$5) same capacit\$5 - 3 5701088.bi,uref. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPAT; USPAT; USPA	-	1	"4681451".PN.	1	2002/12/09 11:50
("metal-insulator-semiconductor") or ("MIS")) same ((("C-V") or (CV) or (Capacits4) dy voltage) or (capacits4)					
("MIS")) same ((("C-V") or (CV) or (capacit\$4 adj voltage) or (capacit\$4 voltage) or (capacit\$4 voltage) or (capacit\$4 voltage) near3 (capacit\$4 voltage) near3 (capacit\$4 voltage) near3 (capacit\$5) same capacit\$5 - 3 5701088.bi,uref. - 4 "6177826" - 4 "6177826" - 23 "5175445" - 23 "5175445" - 3 (("6177826") or ("5175445") or ("5107137")).PN. - 14 5233291.bi,uref. - 2 5233291.pn. - 1 "5065103".PN. CV) or (CV) or (EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; JPO; JPO; JPO; JPO; JPO; JPO; J	-	72	• • • • • • • • • • • • • • • • • • •	1	2002/12/09 14:03
C(apacit\$4 adj voltage) or (capacit\$4-voltage) or (capacit\$4/voltage)) near3 characteristic\$5) same capacit\$5	1			1	
Capacit\$4-voltage) or (capacit\$4/voltage) near3 characteristic\$5) same capacit\$5					
Capacit\$4/voltage) near3				1	
- 3 characteristic\$5) same capacit\$5 5701088.bi,uref. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB USPAT; US-PGPUB EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_				TDM_LDR	
- 3 5701088.bi,uref.					
US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀR; ("5107137")).PN. US-PGPUB USPĀR; US-PGPUB USPĀR; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀR; US-PGPUB USPĀR; US-PGPUB	1_	,		IISPAT:	2002/12/09 13:37
EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB	-	3	STOTOGO.DI, diet.		2502/12/05 15.57
DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB USPĀT; US-PGPUB USPĀT; US-PGPUB USPĀT; US-PGPUB EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB					
- 4 "6177826" USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB USPAT; US-PGPUB					
- 4 "6177826" USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB USPĀT; US-PGPUB USPĀT; US-PGPUB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB USPĀT; US-PGPUB					
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB	-	4	"6177826"		2002/12/09 12:34
EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB USPAT; US-PGPUB					
- 23 "5175445" - 23 "5175445" - 3 (("6177826") or ("5175445") or ("5107137")).PN. - 14 5233291.bi,uref. - 2 5233291.pn. - 1 "5065103".PN. IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB					
- 23 "5175445" USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB				1	
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB					
EPO; JPO; DERWENT; IBM_TDB ("6177826") or ("5175445") or USPAT; US-PGPUB ("5107137")).PN. 14 5233291.bi,uref. 2 5233291.pn. 2 5233291.pn. 1 "5065103".PN. EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB	-	23	"5175445"	1	2002/12/09 12:35
DERWENT; IBM_TDB USPAT; US-PGPUB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB	1			1	
- 3 (("6177826") or ("5175445") or ("5107137")).PN 14 5233291.bi,uref. - 2 5233291.pn. 2 5233291.pn. 1 "5065103".PN. IBM_TDB USPAT; US-PGPUB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB				1	
- 3 (("6177826") or ("5175445") or ("5107137")).PN. - 14 5233291.bi,uref. - 2 5233291.pn. - 2 5233291.pn. - 3 (("6177826") or ("5175445") or USPĀT; US-PGPUB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB - 1 "5065103".PN. - 1 "5065103".PN. - 2 002/12/09 14:00				1	
- 14 ("5107137")).PN. - 14 5233291.bi,uref. - 2 5233291.pn. - 2 5233291.pn. - 3 5233291.pn. - 4 1 "5065103".PN. - 5233291.bi,uref. - 5233291.pn. - 523329		_	//UG177026U\ om /UE175445U\	_	2002/12/00 12:25
- 14 5233291.bi,uref. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB	1 -	3	'	1	2002/12/09 12:35
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB	_	1 1	l '		2002/12/09 14.00
EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB	-	14	J2JJ291.D1, UIEL.	1	2002/12/05 14:00
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB USPAT; US-PGPUB USPAT; US-PGPUB	1			1	
- 2 5233291.pn. IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB USPAT; USPAT	1			1 '	
- 2 5233291.pn. USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB					
US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB 2002/12/09 14:00	_	2	5233291.pn.		2002/12/10 10:03
DERWENT; IBM_TDB USPAT; US-PGPUB DERWENT; IBM_TDB USPAT; US-PGPUB		_		1	
- 1 "5065103".PN. IBM_TDB USPAT; US-PGPUB 2002/12/09 14:00				1	
- 1 "5065103".PN. USPĀT; US-PGPUB 2002/12/09 14:00					
US-PGPUB					
	-	1	"5065103".PN.	•	2002/12/09 14:00
- 1 "4992728".PN. USPAT; 2002/12/09 14:01					
!	-	1	"4992728".PN.		2002/12/09 14:01
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-	1	"4941753".PN.	USPAT; US-PGPUB	2002/12/09 14:01
-	1	"4891584".PN.	USPAT; US-PGPUB	2002/12/09 14:01
_	154	(("metal/insulator/semiconductor") or	USPAT;	2002/12/09 14:05
		("metal-insulator-semiconductor")or	US-PGPUB;	
		("MIS")) same (("C-V") or (CV) or	EPO; JPO;	
		(capacit\$4 adj voltage) or	DERWENT;	
		(capacit\$4-voltage) or	IBM_TDB	
		<pre>(capacit\$4/voltage)) and characteristic\$5 and capacit\$5</pre>		
_	155		USPAT;	2002/12/10 10:12
ļ		("metal-insulator-semiconductor")or	US-PGPUB;	
		("MIS") or ("MAIS")) same (("C-V") or (CV)	EPO; JPO;	ļ
		or (capacit\$4 adj voltage) or	DERWENT;	
		<pre>(capacit\$4-voltage) or (capacit\$4/voltage)) and characteristic\$5</pre>	IBM_TDB	
		and capacit\$5		
_	12	((("metal/insulator/semiconductor") or	USPAT;	2002/12/09 14:35
		("metal-insulator-semiconductor")or	US-PGPUB;	
		("MIS") or ("MAIS")) same (("C-V") or (CV)	EPO; JPO;	
		or (capacit\$4 adj voltage) or	DERWENT;	
		<pre>(capacit\$4-voltage) or (capacit\$4/voltage)) and characteristic\$5</pre>	IBM_TDB	
		and capacit\$5) and synthesis		
-	53		USPAT;	2002/12/09 14:43
		("metal-insulator-semiconductor")or	US-PGPUB;	
		("MIS") or ("MAIS")) same (("C-V") or (CV)	EPO; JPO;	
		or (capacit\$4 adj voltage) or	DERWENT;	
		(capacit\$4-voltage) or (capacit\$4/voltage)) and characteristic\$5	IBM_TDB	
		and capacit\$5) and "nm"		
_	1	I -	USPAT;	2002/12/09 15:29
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	2	5233292.pn.	USPAT;	2002/12/09 15:30
	_		US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
1_	2	5233291.pn.	USPAT;	2002/12/09 15:43
		323231.pm.	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
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-	0	((("metal/insulator/semiconductor") or ("metal-insulator-semiconductor") or	USPAT; US-PGPUB;	2002/12/03 13:44
		("MIS") or ("MAIS")) same (("C-V") or (CV)	EPO; JPO;	
		or (capacit\$4 adj voltage) or	DERWENT;	
		(capacit\$4-voltage) or	IBM_TDB	
		(capacit\$4/voltage)) and characteristic\$5		
1		and capacit\$5) and (("4083254".PN. or three) adj nm)		
_	9	1	USPAT;	2002/12/10 07:14
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			EPO; JPO;	
			DERWENT;	
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1-	1	5233291.pn. and MIS	US-PGPUB;	2002/12/10 07.27
			EPO; JPO;	
			DERWENT;	
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-	6860	motohiro.in.	USPAT; US-PGPUB;	2002/12/10 07:27
1			EPO; JPO;	
İ			DERWENT;	
			IBM TDB	

	6828	motohiro.inv.	USPAT;	2002/12/10 07:28
-	6826	motonito.inv.	US-PGPUB;	2002/12/10 07.28
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
l _	6	motohiro.inv. and ("MAIS")	USPAT;	2002/12/10 07:50
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			EPO; JPO;	
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-	6	motohiro.inv. and ("MAIS")	USPAT;	2002/12/10 07:50
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
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			US-PGPUB;	
			EPO; JPO;	
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_		5233291.pn. and switch\$5	US-PGPUB;	2002/12/10 10.11
	,		EPO; JPO;	
			DERWENT;	
			IBM TDB	
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		Jessessiem. and Belebers	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	155	(("metal/insulator/semiconductor") or	USPĀT;	2002/12/10 10:13
		("metal-insulator-semiconductor")or	US-PGPUB;	
1		("MIS") or ("MAIS")) same (("C-V") or (CV)	EPO; JPO;	
		or (capacit\$4 adj voltage) or	DERWENT;	
		(capacit\$4-voltage) or	IBM_TDB	
		(capacit\$4/voltage)) and characteristic\$5		
		and capacit\$5		2002/12/10 10:15
-	107		USPAT;	2002/12/10 10:15
		("metal-insulator-semiconductor")or	US-PGPUB;	
		("MIS") or ("MAIS")) same (("C-V") or (CV)	EPO; JPO; DERWENT;	
İ		or (capacit\$4 adj voltage) or (capacit\$4-voltage) or	IBM TDB	
		(capacit\$4/voltage)) and characteristic\$5	-5:	
		and capacit\$5) and (switch\$5 or select\$5)		
_	54	• · · · · · · · · · · · · · · · · · · ·	USPAT;	2002/12/10 10:28
		("metal-insulator-semiconductor")or	US-PGPUB;	
		("MIS") or ("MAIS")) same (("C-V") or (CV)	EPO; JPO;	
		or (capacit\$4 adj voltage) or	DERWENT;	
	1	(capacit\$4-voltage) or	IBM_TDB	
	·	(capacit\$4/voltage)) and characteristic\$5		
		and capacit\$5) and ((switch\$5 or		
		select\$5) same (capacit\$5))		0000/10/10 10 10
-	122		USPAT;	2002/12/10 10:30
		("metal-insulator-semiconductor")or	US-PGPUB;	
		("MIS") or ("MAIS")) same (("C-V") or (CV)	EPO; JPO;	
		or (capacit\$4 adj voltage) or	DERWENT;	
		(capacit\$4-voltage) or	IBM_TDB	
		(capacit\$4/voltage)) and characteristic\$5 and capacit\$5) and ((switch\$5 or select\$5		
		or elect\$5) same (capacit\$5))		
	<u> </u>	or erectable and (cabacitable)	<u> </u>	L

-	68	<pre>(((("metal/insulator/semiconductor") or ("metal-insulator-semiconductor")or</pre>	USPAT; US-PGPUB;	2002/12/10 10:54
		("MIS") or ("MAIS")) same (("C-V") or (CV) or (capacit\$4 adj voltage) or	EPO; JPO; DERWENT;	
		(capacit\$4-voltage) or	IBM TDB	
		(capacit\$4/voltage)) and characteristic\$5		
		and capacit\$5) and ((switch\$5 or select\$5		
		<pre>or elect\$5) same (capacit\$5))) not (((("metal/insulator/semiconductor") or</pre>		
		("metal-insulator-semiconductor") or		
		("MIS") or ("MAIS")) same (("C-V") or (CV)		
		or (capacit\$4 adj voltage) or		
		<pre>(capacit\$4-voltage) or (capacit\$4/voltage)) and characteristic\$5</pre>		
		and capacit\$5) and ((switch\$5 or		
		select\$5) same (capacit\$5)))		0000/10/10 10 57
-	31	((silicon adj oxide) near2 thickness) near2 (("3" or three) adj "nm")	USPAT; US-PGPUB;	2002/12/10 10:57
		nearz ((3 or three) adj imi)	EPO; JPO;	
1			DERWENT;	
			IBM_TDB	2002/12/10 11:15
-	13	(((silicon adj oxide) near2 thickness) near2 (("3" or three) adj "nm")) and	USPAT; US-PGPUB;	2002/12/10 11:15
		@ad<20001212	EPO; JPO;	
			DERWENT;	
	6	((((silicon adj oxide) near2 thickness)	IBM_TDB USPAT;	2002/12/10 11:24
_	0	near2 (("3" or three) adj "nm")) and	US-PGPUB;	2002/12/10 11.24
		@ad<20001212) and capacit\$5	EPO; JPO;	
			DERWENT; IBM TDB	
_	2	jp-11150246-\$.did.	USPAT;	2002/12/10 12:46
	_ '		US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
-	1	("5233291").PN.	USPĀT;	2002/12/10 13:07
	,	(HAE10516H) DN	US-PGPUB USPAT;	2002/12/10 13:10
-	1	("4510516").PN.	US-PGPUB	2002/12/10 13.10
_	1	("5568252").PN.	USPAT;	2002/12/10 13:14
	1	("5266892").PN.	US-PGPUB USPAT;	2002/12/10 13:16
-	1	("5200092).FN.	US-PGPUB	2002/12/10 13:10
_	1	("5360989").PN.	USPAT;	2002/12/10 13:17
		/#2646527#\ DN	US-PGPUB USPAT;	2002/12/10 13:17
-	1	("3646527").PN.	US-PGPUB	2002,12,10 13.17
-	2	(("5654588") or ("5973504")).PN.	USPAT	2004/02/17 14:44
-	0	5654588.pn. and (silicon near3 oxide)	USPAT; US-PGPUB;	2004/02/18 14:52
			EPO; JPO;	
			DERWENT;	
	_	ESEASOO no and (cilican near) thickness	IBM_TDB USPAT;	2004/02/18 14:52
-	0	5654588.pn. and (silicon near3 thickness)	US-PGPUB;	2004/02/10 14.32
			EPO; JPO;	
			DERWENT; IBM TDB	
_	0	5654588.pn. and (silicon same thickness)	USPAT;	2004/02/18 14:52
		, , , , , , , , , , , , , , , , , , , ,	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
-	1	5654588.pn. and (thickness)	USPAT;	2004/02/18 14:52
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
		An angelone and the second and the s		